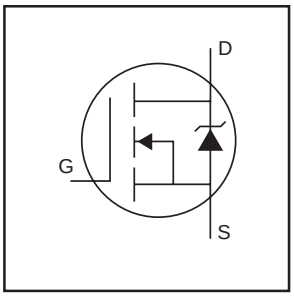
International
IOR Rectifier

PD - 91257D

IRLML2402

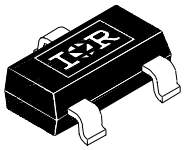
HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- N-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching



V_{DSS} = 20V

$R_{DS(on)}$ = 0.25Ω



Micro3

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

A customized leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards.

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 4.5V	1.2	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 4.5V	0.95	
I_{DM}	Pulsed Drain Current ①	7.4	
P_D@T_A = 25°C	Power Dissipation	540	mW
	Linear Derating Factor	4.3	mW/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

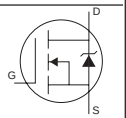
	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	—	230	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	–––	–––	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.024	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	0.25	Ω	V_{GS} = 4.5V, I_D = 0.93A ③
		–––	–––	0.35		V_{GS} = 2.7V, I_D = 0.47A ③
$V_{GS(th)}$	Gate Threshold Voltage	0.70	–––	–––	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	1.3	–––	–––	S	V_{DS} = 10V, I_D = 0.47A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	1.0	µA	V_{DS} = 16V, V_{GS} = 0V
		–––	–––	25		V_{DS} = 16V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	-100	nA	V_{GS} = -12V
	Gate-to-Source Reverse Leakage	–––	–––	100		V_{GS} = 12V
Q_g	Total Gate Charge	–––	2.6	3.9	nC	I_D = 0.93A
Q_{gs}	Gate-to-Source Charge	–––	0.41	0.62		V_{DS} = 16V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	1.1	1.7		V_{GS} = 4.5V, See Fig. 6 and 9 ③
$t_{d(on)}$	Turn-On Delay Time	–––	2.5	–––	ns	V_{DD} = 10V
t_r	Rise Time	–––	9.5	–––		I_D = 0.93A
$t_{d(off)}$	Turn-Off Delay Time	–––	9.7	–––		R_G = 6.2Ω
t_f	Fall Time	–––	4.8	–––		R_D = 11Ω, See Fig. 10 ③
C_{iss}	Input Capacitance	–––	110	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	51	–––		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	–––	25	–––		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	0.54	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	7.4		
V_{SD}	Diode Forward Voltage	–––	–––	1.2	V	T_J = 25°C, I_S = 0.93A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	–––	25	38	ns	T_J = 25°C, I_F = 0.93A
Q_{rr}	Reverse RecoveryCharge	–––	16	24	nC	di/dt = 100A/µs ③



Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② I_{SD} ≤ 0.93A, di/dt ≤ 90A/µs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C

③ Pulse width ≤ 300µs; duty cycle ≤ 2%.

④ Surface mounted on FR-4 board, t ≤ 5sec.

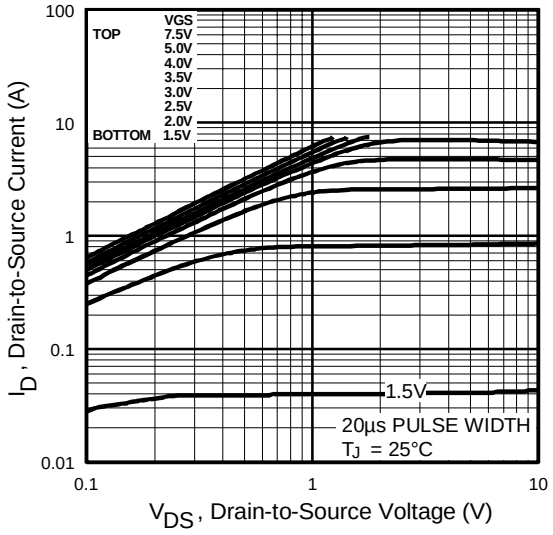


Fig 1. Typical Output Characteristics

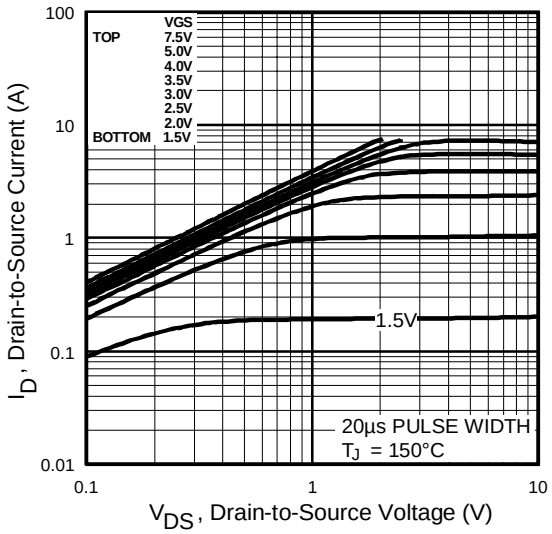


Fig 2. Typical Output Characteristics

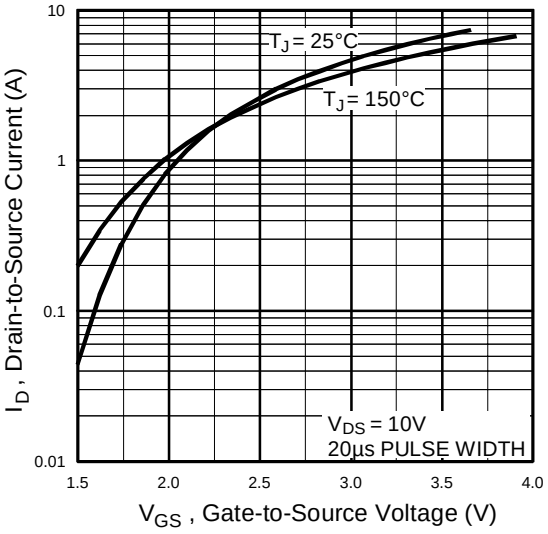


Fig 3. Typical Transfer Characteristics

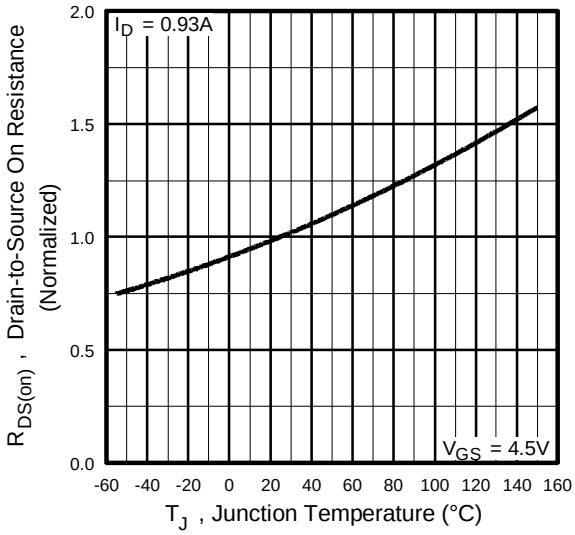


Fig 4. Normalized On-Resistance Vs. Temperature

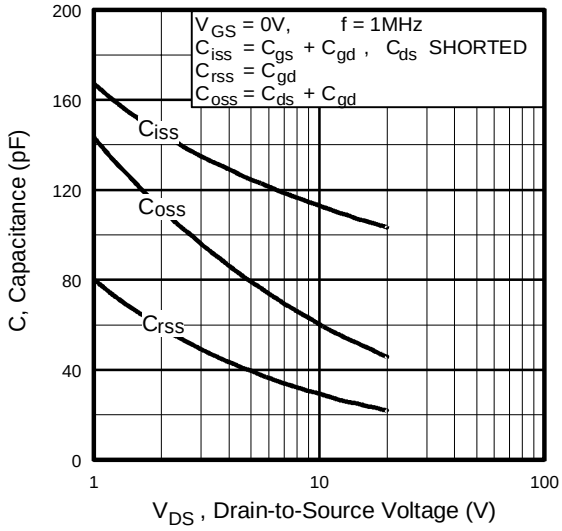


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

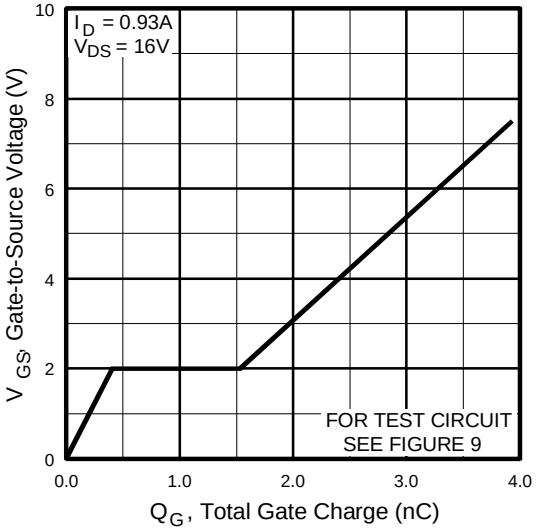


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

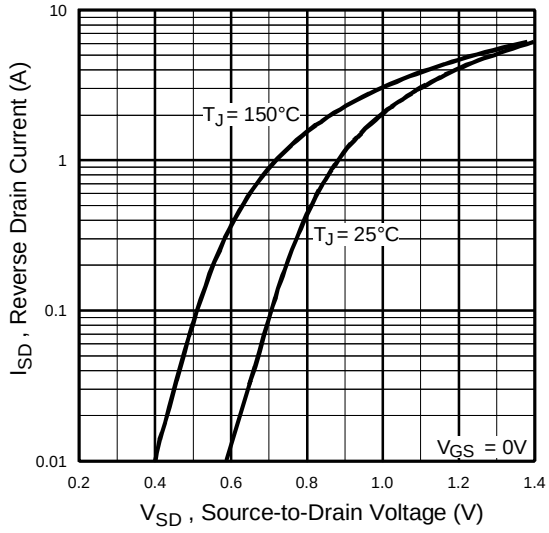


Fig 7. Typical Source-Drain Diode Forward Voltage

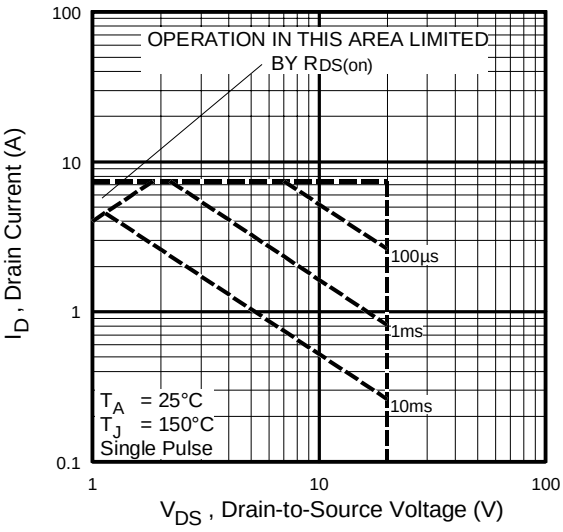


Fig 8. Maximum Safe Operating Area

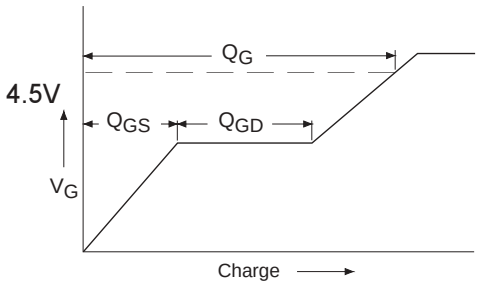


Fig 9a. Basic Gate Charge Waveform

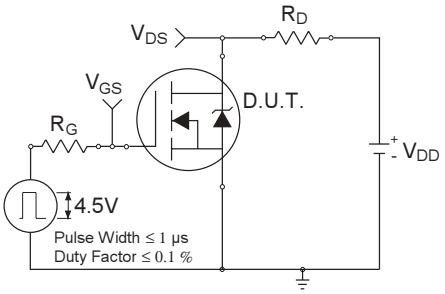


Fig 10a. Switching Time Test Circuit

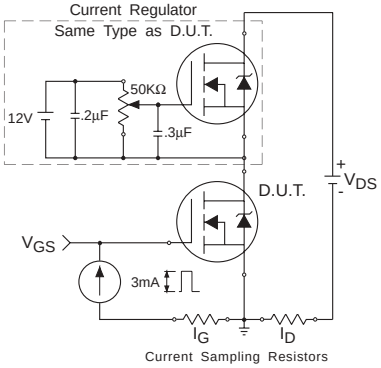


Fig 9b. Gate Charge Test Circuit

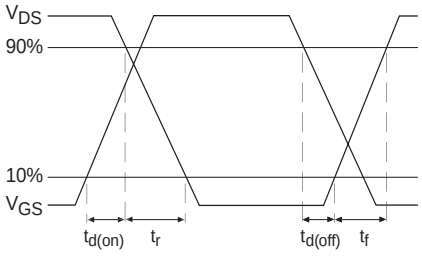


Fig 10b. Switching Time Waveforms

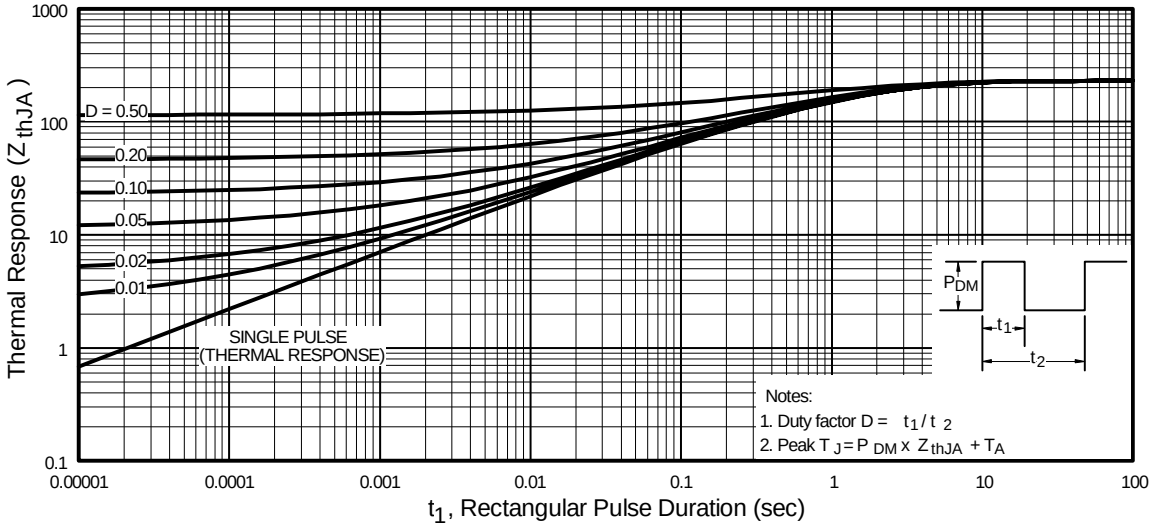
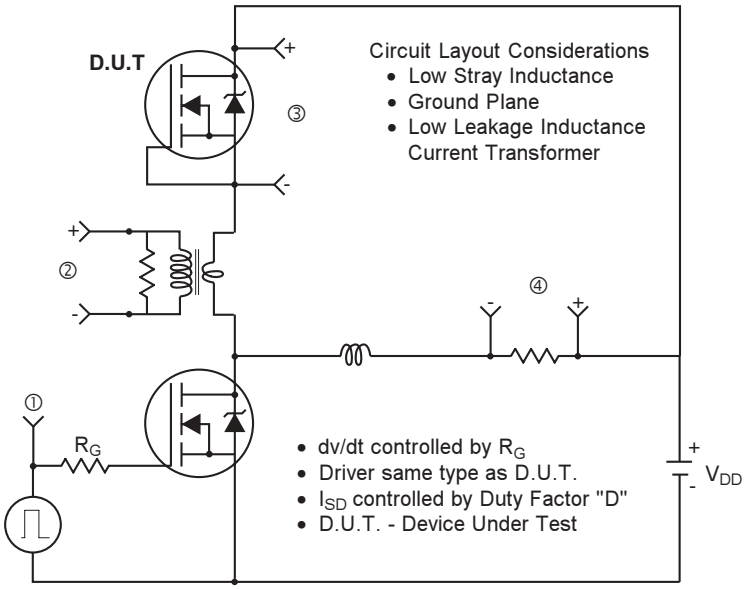
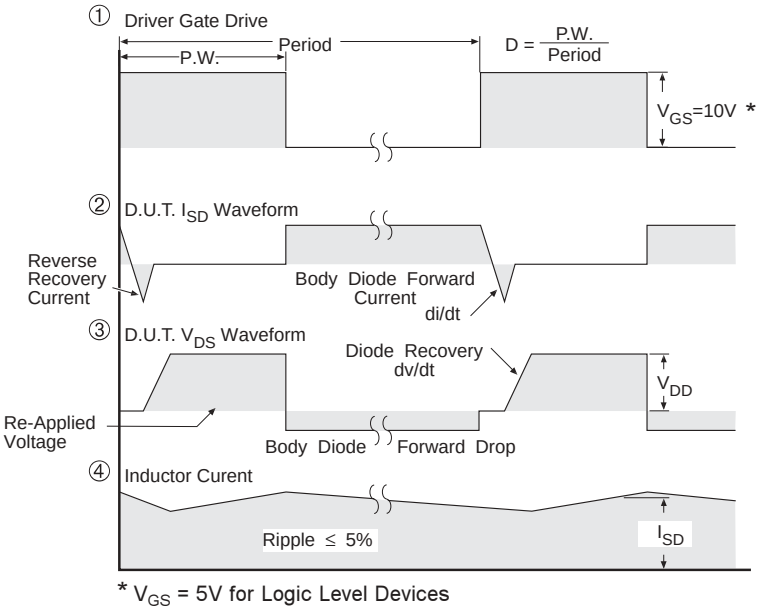


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Peak Diode Recovery dv/dt Test Circuit





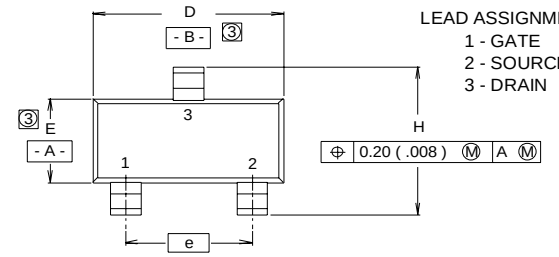
* V_{GS} = 5V for Logic Level Devices

Fig 12. For N-Channel HEXFETS

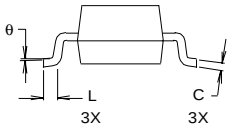
Package Outline

Micro3 (SOT-23 / TO-236AB)

Dimensions are shown in millimeters (inches)

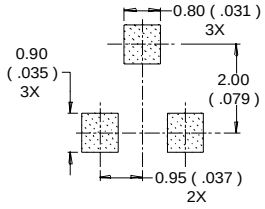


LEAD ASSIGNMENTS
1 - GATE
2 - SOURCE
3 - DRAIN



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.032	.044	0.82	1.11
A1	.001	.004	0.02	0.10
B	.015	.021	0.38	0.54
C	.004	.006	0.10	0.15
D	.105	.120	2.67	3.05
e	.0750 BASIC		1.90 BASIC	
e1	.0375 BASIC		0.95 BASIC	
E	.047	.055	1.20	1.40
H	.083	.098	2.10	2.50
L	.005	.010	0.13	0.25
θ	0°	8°	0°	8°

MINIMUM RECOMMENDED FOOTPRINT



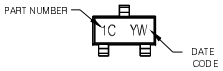
NOTES:
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION : INCH.
3. DIMENSIONS DO NOT INCLUDE MOLD FLASH.

Part Marking Information

Micro3 (SOT-23 / TO-236AB)

Notes: This part marking information applies to devices produced before 02/26/2001

EXAMPLE: THIS IS AN IRLML6302



PART NUMBER CODE REFERENCE:

1A = IRLML2402
1B = IRLML2803
1C = IRLML6302
1D = IRLML5103
1E = IRLML6402
1F = IRLML6401
1G = IRLML2502
1H = IRLML5203

DATE CODE EXAMPLES:

YWW = 9503 = 5C
YWW = 9532 = EF

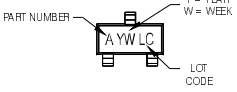
WW = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
1994	4	04	D
1995	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

WW = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

Notes: This part marking information applies to devices produced after 02/26/2001



PART NUMBER CODE REFERENCE:

A = IRLML2402
B = IRLML2803
C = IRLML6302
D = IRLML5103
E = IRLML6402
F = IRLML6401
G = IRLML2502
H = IRLML5203

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
1994	4	04	D
1995	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

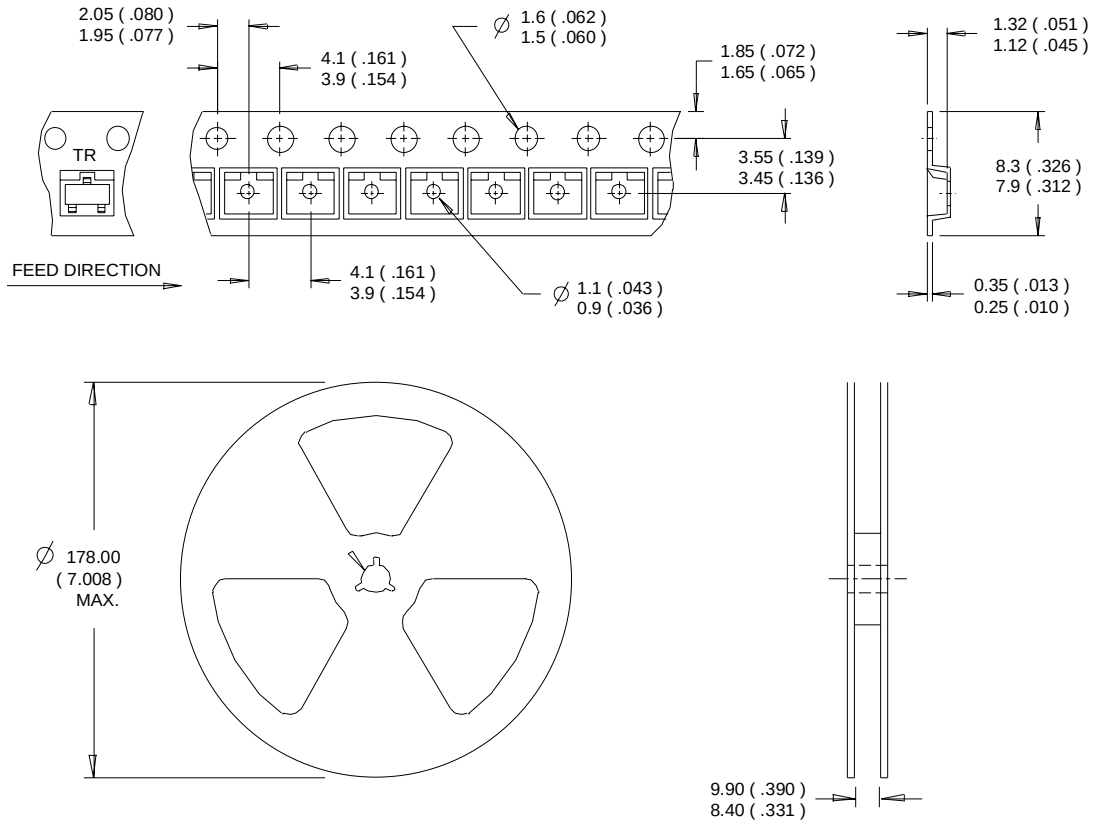
W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

Tape & Reel Information

Micro3 (SOT-23 / TO-236AB)

Dimensions are shown in millimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

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